## TSM70NB1R4CP

Taiwan Semiconductor

# **N-Channel Power MOSFET**

700V, 3A, 1.4Ω

#### FEATURES

- Super-Junction technology
- High performance, small  $R_{DS(ON)}^*Q_g$  figure of merit (FOM)
- High ruggedness performance
- 100% UIS and R<sub>g</sub> tested
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

#### APPLICATION

- Power Supply
- AC/DC LED Lighting

KEY PERFORMANCE PARAMETERS					
PARAMETER VALUE UNIT					
V <sub>DS</sub>	700	V			
R <sub>DS(on)</sub> (max)	1.4	Ω			
Qg	7.4	nC			







Note: MSL 3 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	700	V	
Gate-Source Voltage		$V_{GS}$	±30	V	
Continuous Drain Current (Note 1)	$T_c = 25^{\circ}C$	- I <sub>D</sub>	3	•	
	$T_{\rm C} = 100^{\circ}{\rm C}$		1.8	A	
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	9	А	
Total Power Dissipation @ $T_c = 25^{\circ}C$		P <sub>DTOT</sub>	28	W	
Single Pulsed Avalanche Energy (Note 3)		E <sub>AS</sub>	26	mJ	
Single Pulsed Avalanche Current (Note 3)		I <sub>AS</sub>	0.6	А	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	R <sub>eJC</sub>	4.4	°C/W	
Junction to Ambient Thermal Resistance	R <sub>eja</sub>	62	°C/W	

**Thermal Performance Note:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.

1





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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250 \mu A$	BV <sub>DSS</sub>	700			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V <sub>GS(TH)</sub>	2		4	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 700 V, V_{GS} = 0 V$	I <sub>DSS</sub>			1	μA
Drain-Source On-State Resistance (Note 4)	V <sub>GS</sub> = 10V, I <sub>D</sub> = 1.2A	R <sub>DS(ON)</sub>		1.1	1.4	Ω
Dynamic (Note 5)	L		I	<u> </u>		•
Total Gate Charge		Qg		7.4		
Gate-Source Charge	$V_{DS} = 380V, I_{D} = 3A,$	Q <sub>gs</sub>		1.8		nC
Gate-Drain Charge	V <sub>GS</sub> = 10V	Q <sub>gd</sub>		2.4		
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$	C <sub>iss</sub>		317		
Output Capacitance	f = 1.0MHz	C <sub>oss</sub>		42		pF
Gate Resistance	f = 1.0MHz	R <sub>g</sub>		3.2		Ω
Switching (Note 6)						
Turn-On Delay Time		t <sub>d(on)</sub>		16		
Turn-On Rise Time	$V_{DD} = 380V,$ $R_{GEN} = 25\Omega,$ $I_{D} = 3A, V_{GS} = 10V,$	t <sub>r</sub>		15		
Turn-Off Delay Time		t <sub>d(off)</sub>		26		ns
Turn-Off Fall Time		t <sub>f</sub>		8		
Source-Drain Diode						
Forward On Voltage <sup>(Note 4)</sup>	$I_{\rm S} = 3A, V_{\rm GS} = 0V$	V <sub>SD</sub>			1.4	V
Reverse Recovery Time	$V_{\rm R} = 200 V, I_{\rm S} = 2 A$	t <sub>rr</sub>		137		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q <sub>rr</sub>		0.7		μC

Notes:

1. Current limited by package

2. Pulse width limited by the maximum junction temperature

- 3. L = 144mH, I<sub>AS</sub> = 0.6A, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25 $\Omega$ , Starting T<sub>J</sub> = 25 $^{\circ}$ C
- 4. Pulse test: PW  $\leq$  300µs, duty cycle  $\leq$  2%
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.

#### **ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING
TSM70NB1R4CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel



#### **CHARACTERISTICS CURVES**

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 





#### **CHARACTERISTICS CURVES**

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 





### PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



#### SUGGESTED PAD LAYOUT



#### MARKING DIAGRAM

	5	
	70NB1R4	
	YML	
	75075	
#1	л П	

Υ	= Year Code			
Μ	= Month Code			
	<b>O</b> =Jan	P =Feb	<b>Q</b> =Mar	<b>R</b> =Apr
	<b>S</b> =May	<b>T</b> =Jun	U =Jul	V =Aug
	W =Sep	X =Oct	Y =Nov	Z =Dec
L	= Lot Code (1	~9, A~Z)		



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